

ACKNOWLEDGEMENT RECEIPT

Electronic Version 1.1

Stylesheet Version v1.1.1

Title of Invention

METHOD OF FORMING A LOW VOLTAGE GATE OXIDE LAYER
AND TUNNEL OXIDE LAYER IN AN EEPROM CELL

Submission Type : Information Disclosure
Statement

Application Number:

10/717149



EFS ID:

88332

Server Response:

Confirmation Code	Message
ISVR1	Submission was successfully submitted - Even if Informational or Warning Messages appear below, please do not resubmit this application
ICON1	6780
USPTOEFSNot	For assistance with e-filing a patent application, contact the Patent Electronic Business Center: Toll-Free Number:1(866) 217-9197 Website: http://www.uspto.gov/ebc/

First Named Applicant: Alan Renninger

Attorney Docket Number: ATM-262

Timestamp: 2005-07-18 12:07:55 EDT

From: us

File Listing:

Doc. Name	File Name	Size (Bytes)	Date Produced (yyyymmdd)
us-ids	Atm262-usidst.xml	1765	2005-07-18
us-ids	us-ids.dtd	7763	2005-07-18
us-ids	us-ids.xml	12026	2005-07-18
package-data	Atm262-pkda.xml	1759	2005-07-18
package-data	package-data.dtd	27025	2005-07-18
package-data	us-package-data.xml	19263	2005-07-18
Total files size		69601	

Message Digest: 4a801000924d25574b3ce800ddb074ac8718feeb

Digital Certificate Holder
Name:

cn=Thomas
Schneck,ou=Registered
Attorneys,ou=Patent and
Trademark
Office,ou=Department of
Commerce,o=U.S.
Government,c=US